The RF Line Microwave Pulse Power Transistor

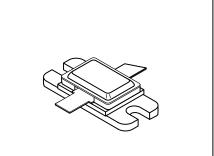
Designed for 1025–1150 MHz pulse common base amplifier applications such as DME.

- Guaranteed Performance @ 1090 MHz Output Power = 500 Watts Peak Gain = 5.2 dB Min
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input Matching
- Characterized with 10 μs, 1.0% Duty Cycle Pulses



Motorola Preferred Device

500 W (PEAK), 1025–1150 MHz MICROWAVE POWER TRANSISTOR NPN SILICON



CASE 355E-01, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	65	Vdc
Collector-Base Voltage	VCBO	65	Vdc
Emitter-Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Peak (1)	IC	35	Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$ (1), (2) Derate above $25^{\circ}C$	PD	1750 10	Watts W/°C
Storage Temperature Range	T _{stg}	T _{stg} -65 to +200	
Junction Temperature	Tj	200	°C

THERMAL CHARACTERISTICS

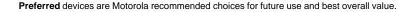
Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case (3)	R _θ JC	0.1	°C/W

NOTES:

1. Under pulse RF operating conditions.

2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.

 Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @32 μs, 2.0%)

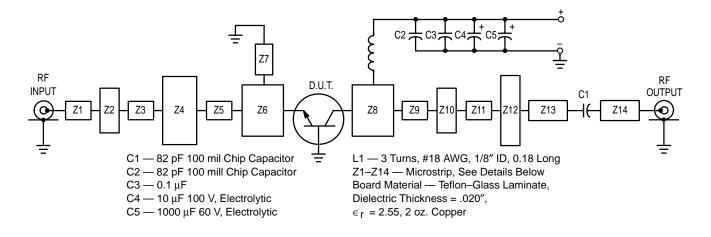




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ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS	•		•	•	•
Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}, V_{BE} = 0$)	V _(BR) CES	70	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}, I_E = 0$)	V(BR)CBO	70	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}, I_C = 0$)	V _{(BR)EBO}	4.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}, I_E = 0$)	ICBO	—	-	40	mAdc
ON CHARACTERISTICS			-	-	•
DC Current Gain (I _C = 5.0 Adc, V_{CE} = 5.0 Vdc)	hFE	20	40	-	_
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	G _{PB}	5.2	-	-	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	η	37	-	-	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz, Load VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power			



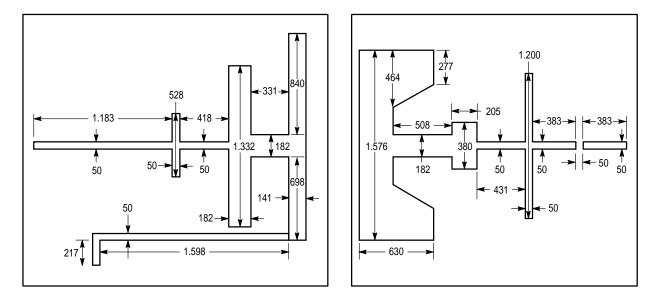
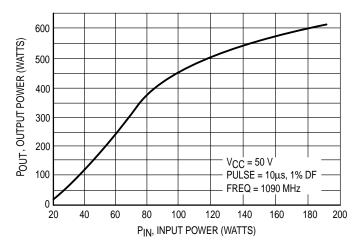
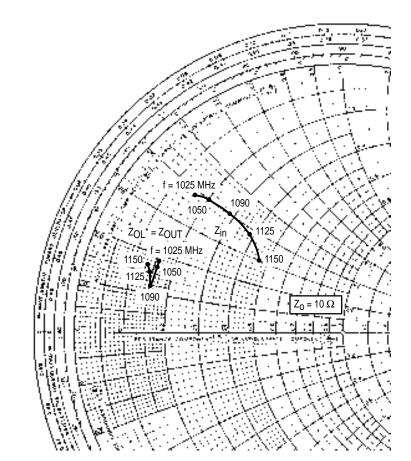


Figure 1. Test Circuit

TYPICAL CHARACTERISTICS

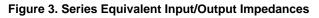




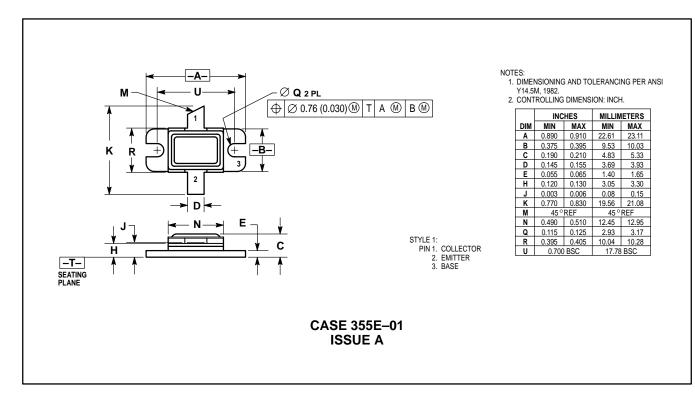


f MHz	Z _{in} OHMS	Z _{OL} *
1025	1.6 + j3.9	1.6 + j1.7
1050	2.0 + j4.0	1.6 + j1.6
1090	2.8 + j4.0	1.5 + j1.1
1125	3.9 + j3.8	1.5 + j1.4
1150	4.6 + j3.0	1.4 + j1.6

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device operates at a given output power, voltage and frequency.



PACKAGE DIMENSIONS



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